

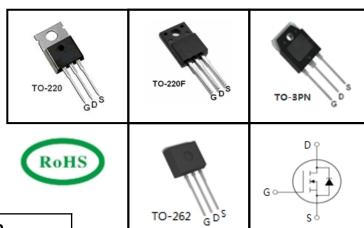
600V Super-Junction Power MOSFET

FEATURES

- $\bullet \quad \text{Very low FOM R}_{\text{DS(on)}} \times \text{Q}_{\text{g}} \\$
- 100% avalanche tested
- RoHS compliant

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information			
Device	Package	Marking	
TPP60R150C	TO-220	60R150C	
TPA60R150C	TO-220F	60R150C	
TPV60R150C	TO-3PN	60R150C	
TPC60R150C	TO-262	60R150C	

Absolute Maximum Ratings $T_C = 25^{\circ}C$, unless otherwise noted				
Barranadar	0	Value		1114
Parameter	Symbol	TO-220, TO-3PN, TO-262	TO-220F	Unit
Drain-Source Voltage (V _{GS} = 0V)	V _{DSS}	600		٧
Continuous Drain Current	I _D	20		А
Pulsed Drain Current (note1)	I _{DM}	60		А
Gate-Source Voltage	V _{GSS}	±30		V
Single Pulse Avalanche Energy (note2)	E _{AS}	480 r		mJ
Avalanche Current (note1)	I _{AR}	4		А
Repetitive Avalanche Energy (note1)	E _{AR}	0.75		mJ
Power Dissipation (T _C = 25°C)	P _D	151 34		W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150		°C

Thermal Resistance				
Dorometer	Symbol	Value		l lm:t
Parameter	Symbol	TO-220, TO-3PN, TO-262	TO-220F	Unit
Thermal Resistance, Junction-to-Case	R _{thJC}	0.83	3.7	00,000
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62	80	°C/W

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TPP60R150C, TPA60R150C, TPV60R150C, TPC60R150C

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		Value				
Parameter	Symbol Test Conditions		Min.	Тур.	Max.	Unit
Static				•		
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_D = 250\mu A$	600			V
Zero Gate Voltage Drain Current		$V_{DS} = 600V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 600V, V_{GS} = 0V, T_{J} = 150^{\circ}C$			100	μA
Gate-Source Leakage	$I_{\rm GSS}$	$V_{GS} = \pm 30V$			±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.5		4.0	V
Drain-Source On-Resistance (Note3)	R _{DS(on)}	V _{GS} = 10V, I _D = 10A		0.13	0.15	Ω
Forward Transconductance (Note3)	g _{fs}	V _{DS} = 10V, I _D = 10A		18.8		S
Dynamic						
Input Capacitance	C _{iss}			2328		pF
Output Capacitance	C _{oss}	$V_{GS} = 0V, V_{DS} = 50V,$ f = 1.0MHz		116		
Reverse Transfer Capacitance	C _{rss}			7		
Total Gate Charge	Q_g			46		nC
Gate-Source Charge	Q_{gs}	$V_{DD} = 480V, I_{D} = 20A, V_{GS} = 10V$		11		
Gate-Drain Charge	Q_{gd}	93		13		
Turn-on Delay Time	t _{d(on)}			43		
Turn-on Rise Time	t _r	$V_{DD} = 400V, I_{D} = 20A,$		14		ns
Turn-off Delay Time	t _{d(off)}	$R_G = 25\Omega$		150		
Turn-off Fall Time	t _f			7		
Drain-Source Body Diode Characteris	stics					
Continuous Body Diode Current	I _s	T 0500			20.6	Δ.
Pulsed Diode Forward Current	I _{SM}	T _C = 25°C			70	A
Body Diode Voltage	V _{SD}	$T_J = 25^{\circ}C$, $I_{SD} = 20A$, $V_{GS} = 0V$		0.9	1.2	V
Reverse Recovery Time	t _{rr}			460		ns
Reverse Recovery Charge	Q _{rr}	$V_R = 480V, I_F = I_S,$ $di_F/dt = 100A/\mu s$		3.8		μC
Peak Reverse Recovery Current	I _{rrm}	3. _F , 3. 100/ v po		35		А

Notes

- 1. Repetitive Rating: Pulse Width limited by maximum junction temperature
- 2. I_{AS} = 4A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}$ C
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 1%



Typical Characteristics $T_J = 25^{\circ}\text{C}$, unless otherwise noted

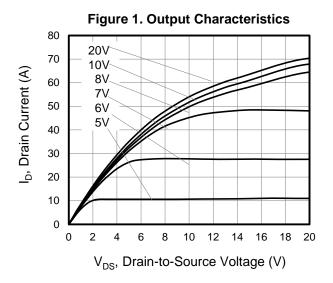


Figure 3. On-Resistance vs. Drain Current

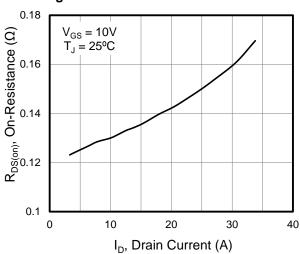


Figure 5. Gate Charge 12 V_{GS}, Gate-to-Source Voltage (V) 10 $V_{DD} = 120V$ 8 6 $V_{DD} = 480V$ 4 2 0 0 10 20 30 50 Q_a, Total Gate Charge (nC)

Figure 2. Transfer Characteristics

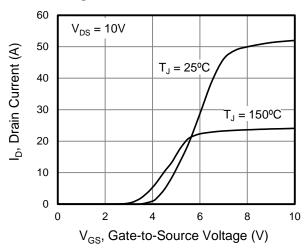


Figure 4. Capacitance

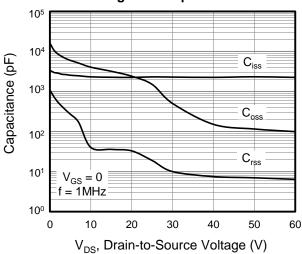


Figure 6. Body Diode Forward Voltage

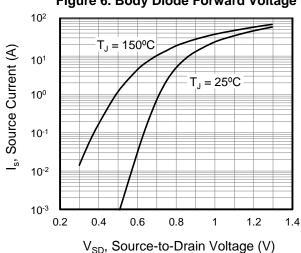




Figure 8. Threshold Voltage vs.

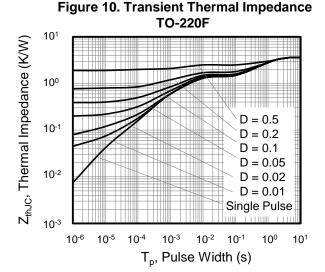
Typical Characteristics $T_J = 25^{\circ}\text{C}$, unless otherwise noted

Figure 7. On-Resistance vs. **Junction Temperature** 3 $V_{GS} = 10V$ 2.5 $I_D = 10A$ R_{DS(on)}, (Normalized) 2 1.5 1 0.5 0 50 -100 100 150 200 T_J, Junction Temperature (°C)

Junction Temperature 0.6 $I_{D} = 250 \mu A$ 0.4 0.2 V_{GS(th)}, (Variance) 0 -0.2 -0.4 -0.6 -0.8 -1 -1.2 -100 -50 100 150 200 T_J, Junction Temperature (°C)

Figure 9. Transient Thermal Impedance TO-220,TO-262/TO-3P **10**0 Z_{thJC}, Thermal Impedance (K/W) 10-1 D = 0.510-2 D = 0.2D = 0.1D = 0.0510-3 D = 0.02D = 0.01Single Pulse 10-4 10⁻⁷ 10-6 10-1

T_p, Pulse Width (s)



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Figure A: Gate Charge Test Circuit and Waveform

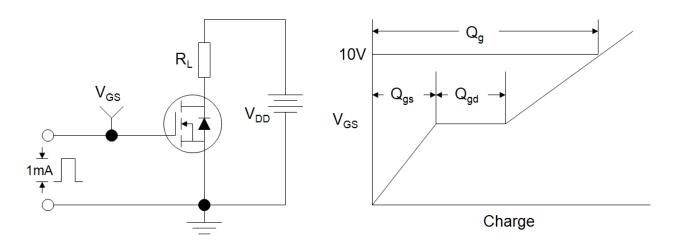


Figure B: Resistive Switching Test Circuit and Waveform

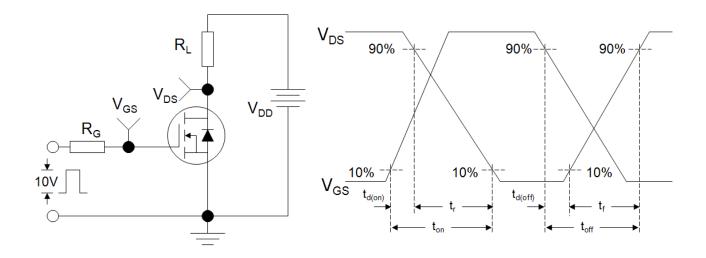
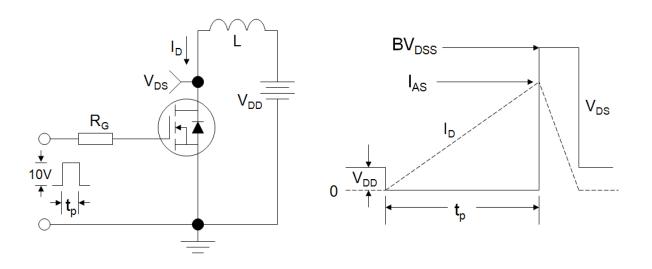


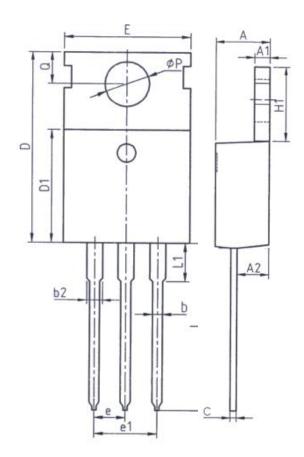
Figure C: Unclamped Inductive Switching Test Circuit and Waveform

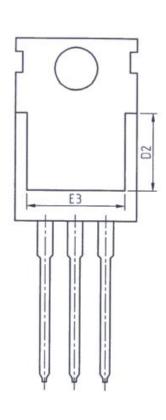


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TO-220

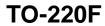


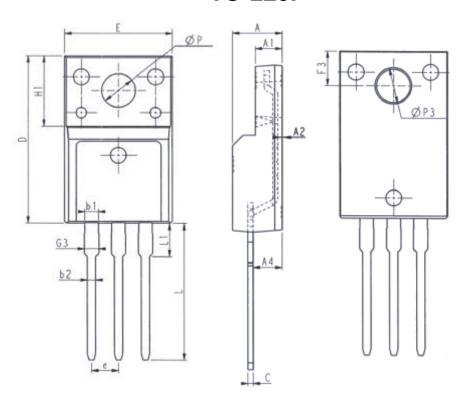


Unit: mm			
Symbol	Min.	Max.	
Α	4. 37	4. 77	
A1	1. 25	1. 45	
A2	2. 20	2. 60	
ь	0. 70	0. 95	
b2	1. 17	1. 47	
С	0. 40	0. 65	
D	15. 10	16. 10	
D1	8. 80	9. 40	
D2	5. 50	_	

Unit: mm			
Symbol	Min.	Max.	
E	9. 70	10. 30	
E3	7. 00	-	
е	2. 54BSC		
e1	5. 08	BBSC	
H1	6. 25	6. 85	
L	12. 75	13.80	
L1	-	3. 40	
P	3. 40	3. 80	
Q	2. 60	3. 00	



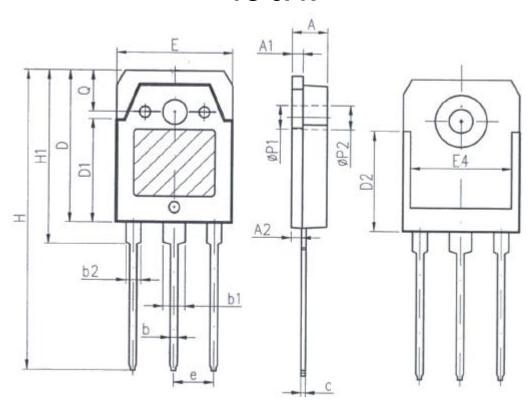




Unit: mm			Unit: mm		
Symbol	Min.	Max.	Symbol	Min.	Max.
E	9.96	10.36	L	12. 68	13. 28
Α	4. 50	4. 90	L1	2. 93	3. 13
A1	2. 34	2. 74	Р	3. 03	3. 38
A2	0.30	0. 60	Р3	3. 15	3. 65
A4	2. 56	2. 96	F3	3. 15	3. 45
С	0. 40	0. 65	G3	1. 25	1. 55
D	15. 57	16. 17	b1	1. 18	1. 43
H1	6. 70REF		b2	0. 70	0. 95
е	2. 54BSC				

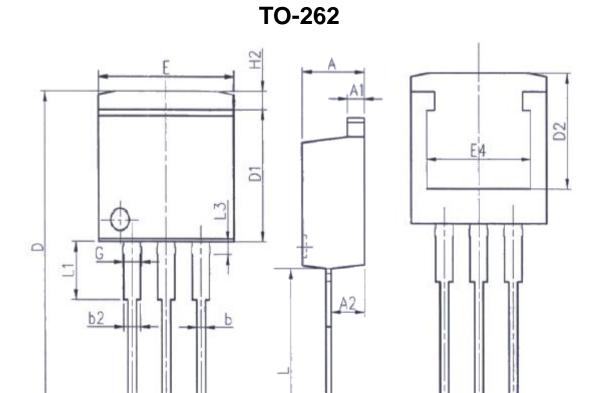


TO-3PN



Unit:mm			
Symbol	Min.	Max.	
Α	4. 6	5	
A1	1. 4	1. 65	
A2	1. 18	1. 58	
b	0.8	1. 2	
b1	2. 8	3. 2	
b2	1.8	2. 2	
С	0.5	0. 75	
D	19. 6	20. 2	
D1	13. 55	14. 25	
D2	12. 9	PREF	
E	15. 35	15. 85	
E4	12. 6	-	
e	5. 45	TYP	
Н	40. 1	40. 9	
H1	23. 15	23. 65	
P1	3. 2REF		
P2	3. 5REF		





Unit: mm			
Symbol	Min.	Max.	
Α	4. 37	4. 77	
A1	1. 22	1. 42	
A2	2. 47	2. 87	
b	0. 70	0. 97	
b2	1. 17	1. 42	
С	0. 28	0.53	
D	23. 20	24. 02	
D1	8. 38	8. 90	
D2	6. 00	-	

Unit: mm			
Symbol	Min.	Max.	
E	9. 90	10.39	
E4	7. 30	_	
е	2. 54BSC		
G	1. 25	1.50	
H2	-	1. 31	
L	13. 34	14. 10	
L1	3. 30	4. 06	
L3	0. 95	1. 15	





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